

NTE2399 MOSFET N–Ch, Enhancement Mode High Speed Switch

Features:

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements

Absolute Maximum Ratings:

Continuous Drain Current ($V_{GS} = 10V$), I_D	
$T_C = +25^\circ C$	3.1A
$T_C = +100^\circ C$	2.0A
Pulsed Drain Current (Note 1), I_{DM}	12A
Power Dissipation ($T_C = +25^\circ C$), P_D	125W
Derate Linearly Above $25^\circ C$	1.0W/ $^\circ C$
Gate-to-Source Voltage, V_{GS}	± 20
Single Pulse Avalanche Energy (Note 2), E_{AS}	280mJ
Avalanche Current (Note 1), I_{AR}	3.1A
Repetitive Avalanche Energy (Note 1), E_{AR}	13mJ
Peak Diode Recovery dv/dt (Note 3), dv/dt	1.0V/ns
Operating Junction Temperature Range, T_J	-55° to $+150^\circ C$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ C$
Lead Temperature (During Soldering, 1.6mm from case for 10sec), T_L	$+300^\circ C$
Mounting Torque (6–32 or M3 Screw)	10 lbf•in (1.1N•m)
Thermal Resistance, Junction-to-Case, R_{thJC}	1.0 $^\circ C/W$
Thermal Resistance, Junction-to-Ambient, R_{thJA}	62 $^\circ C/W$
Typical Thermal Resistance, Case-to-Sink (Flat, Greased Surface), R_{thCS}	0.5 $^\circ C/W$

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 2. $V_{DD} = 50V$, starting $T_J = +25^\circ C$, $L = 55mH$, $R_G = 25\Omega$, $I_{AS} = 3.1A$

Note 3. $I_{SD} \leq 3.1A$, $di/dt \leq 80A/\mu s$, $V_{DD} \leq 600V$, $T_J \leq +150^\circ C$

Note 4. Pules Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	1000	–	–	V
Breakdown Voltage Temp. Coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_J}$	Reference to $+25^\circ\text{C}$, $I_D = 1\text{mA}$	–	1.4	–	V/ $^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.9A$, Note 4	–	–	0.50	Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	–	4.0	V
Forward Transconductance	g_{fs}	$V_{DS} = 100V, I_D = 1.9A$, Note 4	2.1	–	–	mhos
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 1000V, V_{GS} = 0V$	–	–	100	μA
		$V_{DS} = 800V, V_{GS} = 0V, T_J = +125^\circ\text{C}$	–	–	500	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -20V$	–	–	-100	nA
Gate-to-Source Reverse Leakage	I_{GSS}	$V_{GS} = 20V$	–	–	100	nA
Total Gate Charge	Q_g	$I_D = 3.1A, V_{DS} = 400V, V_{GS} = 10V$, Note 4	–	–	80	nC
Gate-to-Source Charge	Q_{gs}		–	–	10	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}		–	–	42	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 500V, I_D = 3.1A, R_G = 12\Omega$, $R_D = 170\Omega$, Note 4	–	12	–	ns
Rise Time	t_r		–	25	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	89	–	ns
Fall Time	t_f		–	29	–	ns
Internal Drain Inductance	L_D	Between lead, .250in. (6.0) mm from package and center of die contact	–	4.5	–	nH
Internal Source Inductance	L_S		–	7.5	–	nH
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$	–	980	–	pF
Output Capacitance	C_{oss}		–	140	–	pF
Reverse Transfer Capacitance	C_{riss}		–	50	–	pF

Source-Drain Ratings and Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	I_S		–	–	3.1	A
Pulsed Source Current (Body Diode)	I_{SM}	Note 1	–	–	12	A
Diode Forward Voltage	V_{SD}	$T_J = +25^\circ\text{C}, I_S = 3.1A, V_{GS} = 0V$, Note 4	–	–	1.8	V
Reverse Recovery Time	t_{rr}	$T_J = +25^\circ\text{C}, I_F = 3.1A$, $di/dt = 100A/\mu s$, Note 4	–	410	620	ns
Reverse Recovery Charge	Q_{rr}		–	1.3	2.0	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 4. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

